2SB1599

Silicon PNP epitaxial planar type

For power amplification
Complementary to 2SD2457

Features

- ullet Low collector to emitter saturation voltage $V_{CE(sat)}$.
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

Absolute Maximum Ratings (Ta=25°C)

| Parameter | Symbol | Ratings | Unit |
|------------------------------|--------------------|-------------------|------|
| Collector to base voltage | V_{CBO} | -50 | V |
| Collector to emitter voltage | V_{CEO} | -40 | V |
| Emitter to base voltage | V_{EBO} | -5 | V |
| Peak collector current | I_{CP} | -3 | A |
| Collector current | I_{C} | -1.5 | A |
| Collector power dissipation | ${P_C}^*$ | 1 | W |
| Junction temperature | T_{j} | 150 | °C |
| Storage temperature | T_{stg} | −55 ~ +150 | °C |

 $^{^\}ast$ Printed circuit board: Copper foil area of 1cm² or more, and the board thickness of 1.7mm for the collector portion

Unit: mm 4.5±0.1 1.6±0.2 1.5±0.1 1.5±0.1 1.5±0.1 1.5±0.1 1.5±0.1 1.5±0.1 1.5±0.1 1.5±0.1 1.5±0.1 MiniP3-F1 Package

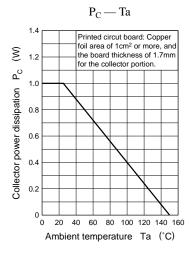
Marking symbol: 1X

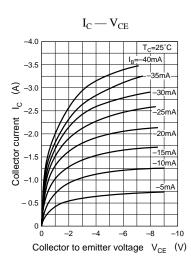
Electrical Characteristics (Ta=25°C)

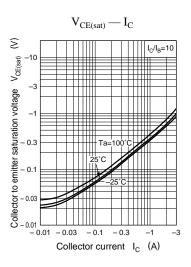
| Parameter | Symbol | Conditions | min | typ | max | Unit |
|---|----------------------|--|-----|-------|------|------|
| C 11 4 66 | I_{CBO} | $V_{CB} = -20V, I_E = 0$ | | | -1 | μΑ |
| Collector cutoff current | I _{CEO} | $V_{CE} = -12V, I_B = 0$ | | | -100 | μΑ |
| Emitter cutoff current | I _{EBO} | $V_{EB} = -5V, I_C = 0$ | | | -100 | μA |
| Collector to base voltage | V _{CBO} | $I_{\rm C} = -1 \text{mA}, \ I_{\rm E} = 0$ | -50 | | | V |
| Collector to emitter voltage | V _{CEO} | $I_{\rm C} = -10 {\rm mA}, I_{\rm B} = 0$ | -40 | | | V |
| Forward current transfer ratio | h _{FE} * | $V_{CE} = -5V, I_{C} = -1A$ | 80 | | 220 | |
| Collector to emitter saturation voltage | V _{CE(sat)} | $I_C = -1.5A, I_B = -0.15A$ | | - 0.4 | -1 | V |
| Base to emitter saturation voltage | V _{BE(sat)} | $I_C = -2A, I_B = -0.2A$ | | | -1.5 | V |
| Transition frequency | f_T | $V_{CB} = -5V$, $I_E = 0.5A$, $f = 200MHz$ | | 150 | | MHz |
| Collector output capacitance | C _{ob} | $V_{CB} = -5V, I_E = 0, f = 1MHz$ | | 70 | | pF |

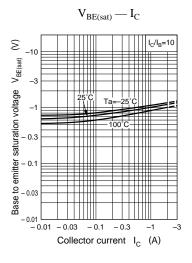
*hFE Rank classification

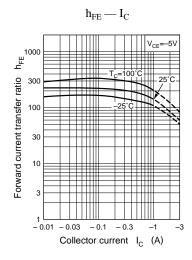
| Rank | Q | R |
|-----------------|----------|-----------|
| h _{FE} | 80 ~ 160 | 100 ~ 220 |

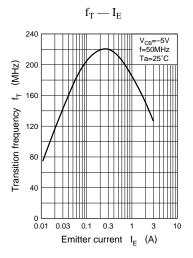


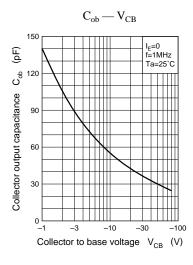


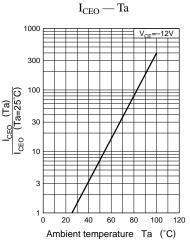












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